a first measurement pattern;

a second measurement pattern to be superimposed on an image of said first measurement pattern; and

an extraction pattern to be used for an extraction of a predetermined image from a superimposed image of said first measurement pattern and said second measurement pattern.

4. (Amended) A mask according to claim 2, wherein said inspection pattern is formed in a separate area to a circuit pattern area in which said circuit pattern is formed.

5. (Amended) A mask according to claim 2, wherein said inspection pattern is a part of said circuit pattern.

6. (Amended) A mask according to claim 2, wherein a line width of said inspection pattern corresponds to a line width of said circuit pattern.

7. (Amended) An exposure method comprising:

an exposure step of transferring a circuit pattern of said mask of claim 2 onto a photosensitive substrate via an optical system; and

a measurement step of measuring prior to said exposure step, using an inspection pattern which is formed on said mask to be used in said exposure step, a line width of a pattern to be transferred to said substrate.

11. (Amended) A mask comprising:

a base member;

a first linear pattern formed on said base member and which has a predetermined line width; and

a second linear pattern which is superimposed on an image of said first linear pattern and has a line width different from that of said first linear pattern.

--15. (New) A mask according to claim 2, wherein said inspection pattern is an isolated pattern.--

--16. (New) A mask according to claim 2, wherein said inspection pattern is a line-and-space pattern.--

--17. (New) A mask comprising:

a base member;

a circuit pattern formed on said base member; and

an inspection pattern formed on said base member, wherein said inspection pattern is formed in a separate area to a circuit pattern area in which said circuit pattern is formed.--

--18. (New) A mask according to claim 17, wherein a line width of said inspection pattern corresponds to a line width of said circuit pattern.--

--19. (New) A mask according to claim 17, wherein said inspection pattern is an isolated pattern.--

--20. (New) A mask according to claim 17, wherein said inspection pattern is a line-and-space pattern.--

--21. (New) A mask according to claim 17, wherein said inspection pattern comprises a first linear pattern formed with a predetermined line width, and a second linear pattern superimposed on an image of said first linear pattern and formed with a line width different from that of said first linear pattern.--

--22. (New) An exposure method comprising:

an exposure step of transferring a circuit pattern of a mask according to claim 17 onto a photosensitive substrate via an optical system; and